



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



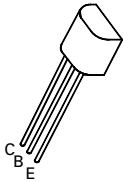
PNP SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

ISSUE 3 – JUNE 94

FEATURES

- * 2 Amps continuous current
- * Up to 5 Amps peak current
- * Very low saturation voltage
- * Excellent gain characteristics up to 2 Amps
- * Spice model available

ZTX956



E-Line
T092 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-6	V
Peak Pulse Current	I_{CM}	-5	A
Continuous Collector Current	I_C	-2	A
Practical Power Dissipation*	P_{totp}	1.58	W
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1.2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-220	-300		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	-220	-300		V	$I_C = -1\mu A$, $R_B \leq 1K\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200	-240		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}			-50 -1	nA μA	$V_{CB} = -200V$ $V_{CB} = -200V$, $T_{amb} = 100^{\circ}C$
Collector Cut-Off Current	I_{CER} $R \leq 1K\Omega$			-50 -1	nA μA	$V_{CB} = -200V$ $V_{CB} = -200V$, $T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-30 -110 -150	-50 -150 -250	mV mV mV	$I_C = -100mA$, $I_B = -10mA^*$ $I_C = 1A$, $I_B = -100mA^*$ $I_C = 2A$, $I_B = -400mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-920	-1050	mV	$I_C = 2A$, $I_B = -400mA$

ZTX956

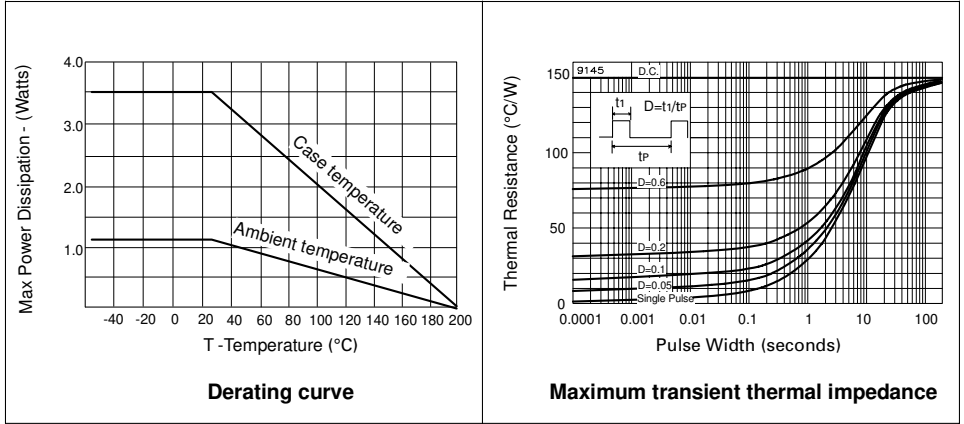
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	V _{BE(on)}		-770	-900	mV	I _C =-2A, V _{CE} =-5V*
Static Forward Current Transfer Ratio	h _{FE}	100 100 50	200 200 150 10	300		I _C =-10mA, V _{CE} =-5V* I _C =-1A, V _{CE} =-5V* I _C =-2A, V _{CE} =-5V* I _C =-5A, V _{CE} =-5V*
Transition Frequency	f _T		110		MHz	I _C =-100mA, V _{CE} =-10V f=50MHz
Output Capacitance	C _{obo}		32		pF	V _{CB} =-20V, f=1MHz
Switching Times	t _{on} t _{off}		67 1140		ns ns	I _C =-1A, I _{B1} =-100mA I _{B2} =100mA, V _{CC} =-50V

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

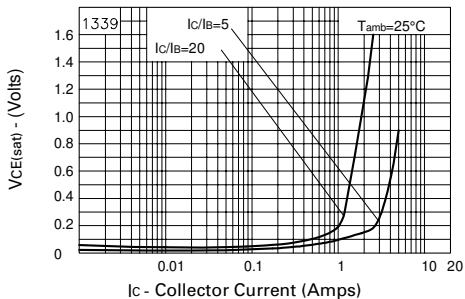
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	R _{th(j-amb)}	150	°C/W
Junction to Case	R _{th(j-case)}	50	°C/W

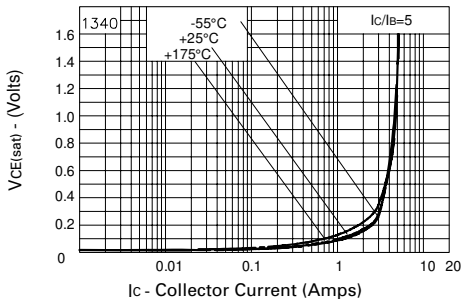


ZTX956

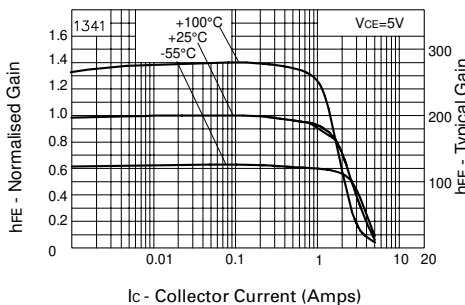
TYPICAL CHARACTERISTICS



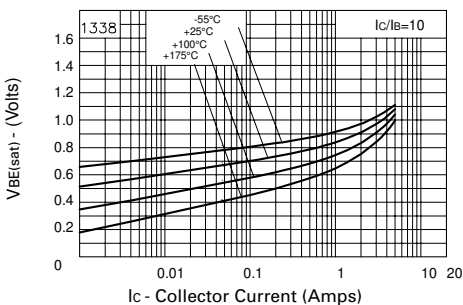
$V_{CE(sat)}$ v I_C



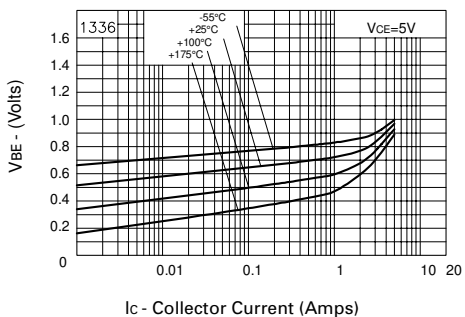
$V_{CE(sat)}$ v I_C



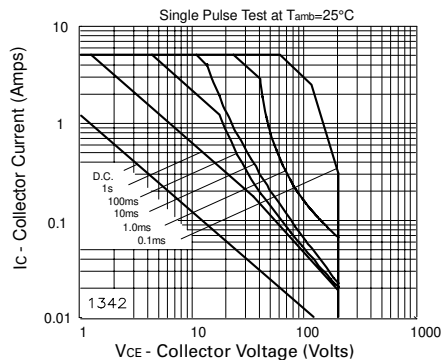
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area